IN THE CLAIMS:

Please CANCEL claims 5-9 without prejudice or disclaimer. Please AMEND various claims and ADD new claims in accordance with the following:

1. (Currently Amended) A manufacturing method for an optical waveguide device, comprising ~~the steps of~~:

forming an optical waveguide in a substrate having an electro-optic effect, said substrate having upper, lower, and side surfaces;

forming an SiO_2 film on said substrate;

forming silicon (Si) ~~Si~~ films on said SiO_2 film, the lower surface of said substrate, and at least a part of the side surface of said substrate to thereby make a conduction between said Si film formed on said SiO_2 film and said Si film formed on the lower surface of said substrate;

applying a photoresist to said Si film formed on said SiO_2 film;

patterning said photoresist so that a portion of said photoresist corresponding to said optical waveguide is left attached on said Si film;

forming a groove on said substrate along said optical waveguide by reactive ion etching; and

removing said photoresist and said Si films.

2. (Currently Amended) The manufacturing method according to claim 1, wherein said substrate comprises a $LiNbO_3$ substrate, and ~~said step of~~ forming said optical waveguide comprises ~~the step of~~ thermally diffusing titanium (Ti) ~~Ti~~ in said $LiNbO_3$ substrate.

3. (Currently Amended) The manufacturing method according to claim 1, wherein said ~~step of~~ forming said Si films is performed by sputtering.

4. (Original) The manufacturing method according to claim 1, wherein said photoresist comprises a conductive photoresist.

5. – 9. (Cancelled).

10. (New) A method for manufacturing an optical waveguide device, comprising:

forming an optical waveguide in a substrate having an electro-optic effect;

forming an SiO_2 film on the substrate;

forming a silicon (Si) film on the SiO_2 film to thereby make a conducting connection between the Si film and the SiO_2 film;

applying a photoresist to the Si film formed on the SiO_2 film;

patterning the photoresist so that a portion of the photoresist corresponding to the optical waveguide is left attached on the Si film;

forming a groove on the substrate along the optical waveguide by reactive ion etching.

11. (New) The manufacturing method according to claim 10, wherein the substrate comprises a $LiNbO_3$ substrate, and said forming the optical waveguide comprises thermally diffusing titanium (Ti) in the $LiNbO_3$ substrate.

12. (New) The manufacturing method according to claim 10, wherein said forming the Si films is performed by sputtering.

13. (New) The manufacturing method according to claim 10, wherein the photoresist comprises a conductive photoresist.

14. (New) A method for manufacturing an optical waveguide device, comprising:

forming an optical waveguide in a substrate having an electro-optic effect;

forming an SiO_2 film on the substrate;

forming a silicon (Si) film on the SiO_2 film to thereby make a conducting connection between the Si film and the SiO_2 film;

applying a photoresist to the Si film formed on the SiO_2 film;

patterning the photoresist so that a portion of the photoresist corresponding to the optical waveguide is left attached on the Si film;

forming a groove on the substrate along the optical waveguide by reactive ion etching; and

the substrate comprises a $LiNbO_3$ substrate, and said forming the optical waveguide comprises thermally diffusing titanium (Ti) in the $LiNbO_3$ substrate.

15. (New) The manufacturing method according to claim 14, wherein forming the Si films is performed by sputtering.

16. (New) The manufacturing method according to claim 14, wherein the photoresist comprises a conductive photoresist.